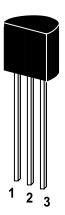
NPN Silicon Epitaxial Planar Transistor

for switching, driver stage and audio frequency low power amplifier applications.

The transistor is subdivided into three groups, O, Y and G, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	35	V
Collector Emitter Voltage	V _{CEO}	30	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	Ic	500	mA
Base Current	I _B	100	mA
Power Dissipation	P _{tot}	500	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	-55 to +150	°С







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Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V _{CE} =1V, I _C =100mA					
Current Gain Group O	h _{FE}	70	-	140	-
Y	h _{FE}	120	-	240	-
G	h _{FE}	200	-	400	-
at V _{CE} =6V, I _C =400mA	h _{FE}	25	-	-	-
Base Emitter Voltage					
at I _C =100mA, V _{CE} =1V	V_{BE}	-	0.8	1	V
Emitter Cutoff Current					
at V _{EB} =5V	I _{EBO}	-	-	0.1	μΑ
Collector Cutoff Current					
at V _{CB} =35V	I _{CBO}	-	-	0.1	μΑ
Collector Saturation Voltage					
at I _C =100mA, I _B =10mA	$V_{CE(sat)}$	-	0.1	0.25	V
Transition Frequency					
at V _{CE} =6V, I _C =20mA	f_T	-	300	-	MHz
Output Capacitance					
at V _{CB} =6V, f=1MHz	Сов	-	7	-	pF







